

ABSTRACT

Chamfering C1 is performed along the edge of a notch groove by the center O1 of a grindstone 5. Change to grindstone center O2 is performed to perform chamfering C2 along the edge of the notch groove. Similarly, chamfering C3, C4 and C5 are formed. A grindstone having a large diameter can be employed. Only control of the diameter of the grindstone is required to maintain the shape. Satisfactory surface roughness can be realized. It is possible to improve surface roughness of a notch groove of a wafer and realize high efficiency.

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